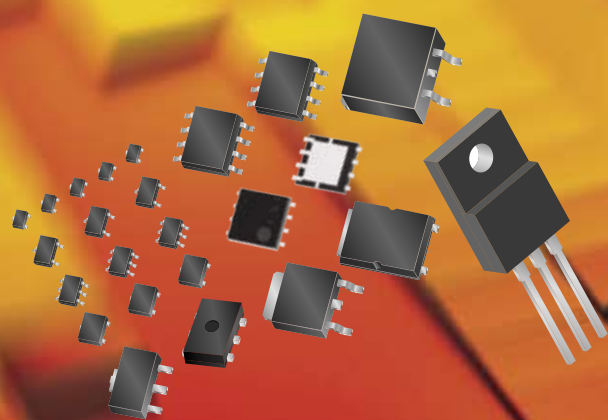




Product Catalog

2009-1st



# ***MOSFETs***

Discretes

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## MOSFETs

### Highlight

- **ECOMOS™ Series**

Portable equipment is increasingly shifting to low voltage drive. This energy-saving series meets those needs.

- **MPT6 Package Dual MOSFETs**

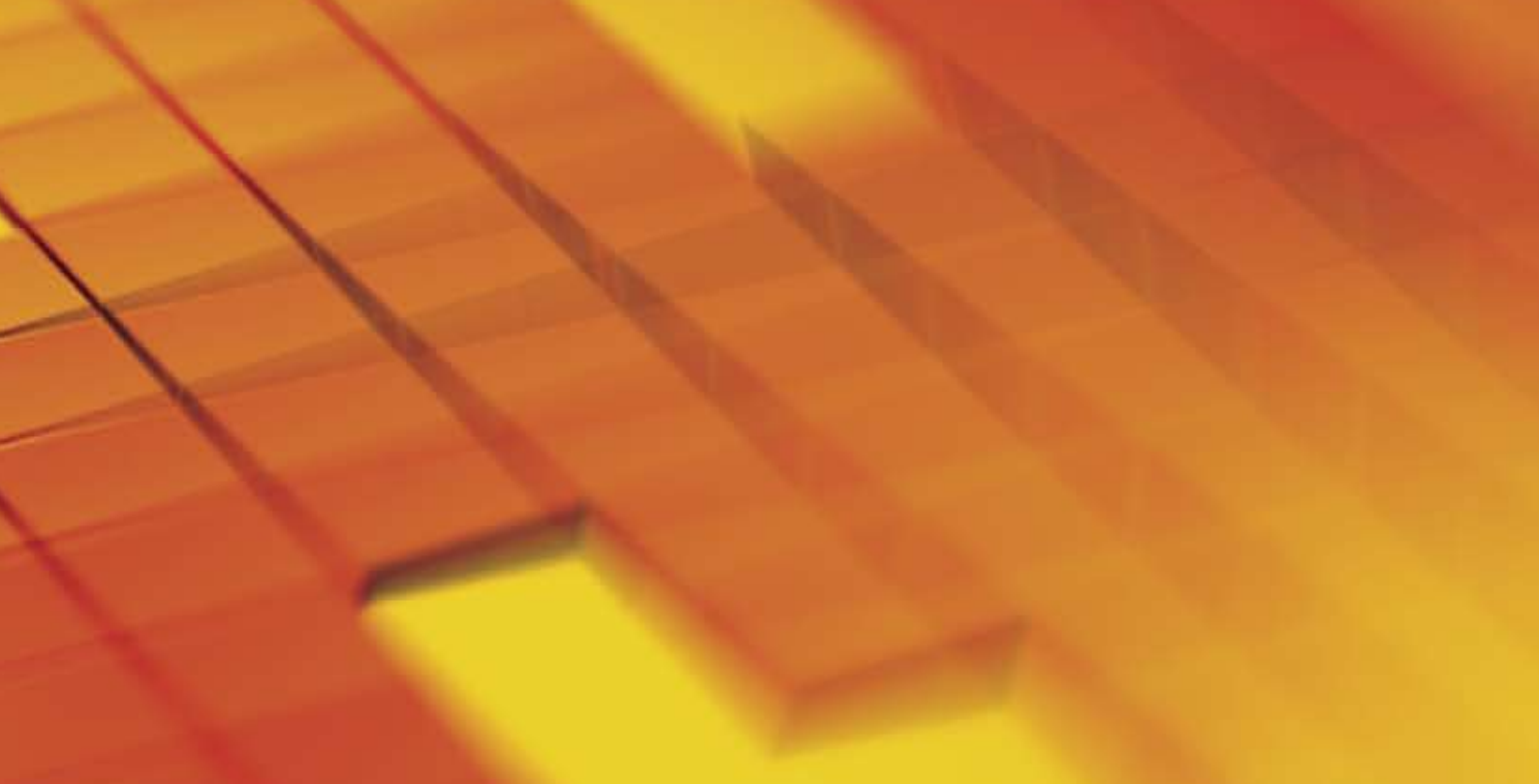
This high-power series features the same package power as conventional SOP8 units, but in a package 40% smaller.

- **TCPT3 Package MOSFETs**

High-power series ;  
The same mounting space as the one for conventional CPT3 package : yet more current is applicable.

- **High-speed Switching High Voltage Resistance MOSFETs**

This high performance, high speed switching series reduces switching loss by 30% compared to conventional products. (500 to 600V)



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**Highlight**

# MOSFET Lineup

ECOMOS™ Series

	Drive Voltage (V)	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)						Package	Page			
			0.2 / 0.3	1 / 1.3	1.5 / 2	2.4 / 2.5	3 / 3.5	4 / 4.5			5 / 6 / 7		
Single type	1.2	20	<b>New</b> RUM002N02(N)							VMT3	P.5		
			<b>New</b> RZM002P02(P)							EMT3			
			<b>New</b> RUE002N02(N)										
			<b>New</b> RZE002P02(P)										
	1.5	12		<b>New</b> RZF013P01(P)	<b>New</b> RZF020P01(P)			RZF030P01(P)		TUMT3	P.6		
						<b>New</b> RZL025P01(P)	RZL035P01(P)		TUMT6				
						<b>New</b> RZR020P01(P)	<b>New</b> RZR025P01(P)		RZR040P01(P)	TSMT3			
				<b>New</b> RW1A013ZP(P)	<b>New</b> RW1A020ZP(P)					WEMT6	P.6		
									<b>New</b> RZQ045P01(P)	<b>RZQ050P01(P)</b>	TSMT6	P.5	
									<b>New</b> RT1A040ZP(P)	<b>New</b> RT1A050ZP(P)	TSST8		
										<b>New</b> RQ1A060ZP(P)	TSMT8	P.6	
										<b>New</b> RQ1A070ZP(P)	TSMT8		
			20				<b>New</b> RUF020N02(N)	<b>New</b> RUF025N02(N)				TUMT3	P.5
									RUL035N02(N)			TUMT6	
						<b>New</b> RUR020N02(N)			<b>New</b> RUR040N02(N)	TSMT3			
									<b>RUQ050N02(N)</b>	TSMT6			
						<b>New</b> RW1C020UN(N)				WEMT6	P.6		
	1.8									VMT3	P.5		
										EMT3			
						RUF015N02(N)			TUMT3				
						<b>New</b> RW1C015UN(N)			WEMT6	P.6			
Dual type	1.2	20	<b>New</b> EM6K7(N+N)							P.5			
			<b>New</b> EM6J1(P+P)						EMT6				
			<b>New</b> EM6M2(P+N)										
	1.5	12		<b>New</b> US6J11(P+P)						TUMT6	P.6		
					<b>New</b> QS6J11(P+P)					TSMT6			
						<b>New</b> TT8J1(P+P)				TSST8			
							<b>New</b> TT8J21(P+P)			TSST8			
	20		<b>New</b> EM6K6(N+N)							EMT6			
						US6K4(N+N)				TUMT6	P.5		
	1.5 / 1.8	12 / 20		<b>New</b> US6M11(P+N)						TUMT6			
Built-in Diode	1.5	12		<b>New</b> ES6U1(P)						WEMT6	P.6		
		20				QS5U36(N)				TSMT5	P.5		
	1.8					<b>New</b> TT8U1(P)				TSST8	P.6		
										WEMT6			

MPT6 Package Dual MOSFETs

	Drive Voltage (V)	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)				Package	Page
			3.5	4.5	5	6		
Dual type	4	30	MP6K65(N+N)		MP6K61(N+N)	MP6K62(N+N)	MPT6	7
			MP6M62(P+N)	MP6M63(P)	MP6M63(N)			

TCPT3 Package MOSFETs

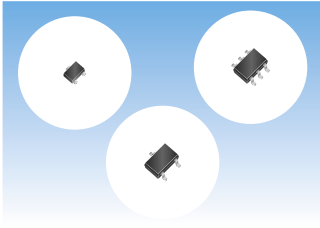
Drive Voltage (V)	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)			Package	Page
		16	20	30		
4	40			RSY300N04(N)	TCPT3	8
	45	RSY160P05(P)	RSY200N05(N)			

High-speed Switching High Voltage Resistance MOSFETs

Drive Voltage (V)	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)								Package	Page	
		4 / 5	6 / 7	8 / 9	10 / 11	12 / 13	15 / 16	18 / 19	20 / 21 / 25			
10	400			<i>New</i> R4008AND(N)							CPT3	P.9
	500		R5007ANJ(N)	R5009ANJ(N)	<i>New</i> R5011ANJ(N)	<i>New</i> R5013ANJ(N)	R5016ANJ(N)	<i>New</i> R5019ANJ(N)	<i>New</i> R5021ANJ(N)		LPT	
		<i>New</i> R5005CNX(N)	R5007ANX(N)	R5009ANX(N)	<i>New</i> R5011ANX(N)	R5013ANX(N)	R5016ANX(N)	<i>New</i> R5019ANX(N)	<i>New</i> R5021ANX(N)		TO-220FM	
	525	<i>New</i> R5205CND(N)	<i>New</i> R5207AND(N)								CPT3	
	600	<i>New</i> R6004AND(N)	<i>New</i> R6006AND(N)								CPT3	
						<i>New</i> R6012ANJ(N)	<i>New</i> R6015ANJ(N)	<i>New</i> R6018ANJ(N)	<i>New</i> R6020ANJ(N)		LPT	
				R6008ANX(N)	<i>New</i> R6010ANX(N)	R6012ANX(N)	<i>New</i> R6015ANX(N)	<i>New</i> R6018ANX(N)	R6020ANX(N)		TO-220FM	
									<i>★</i> R6025ANZ(N)		TO-3PF	

*★*: Under Development

# ECOMOS™ Series ①



## Features

Energy saving

## Summary

The development of a new low voltage drive process has enabled operation at  $V_{GS} = 1.2V$  to  $1.8V$

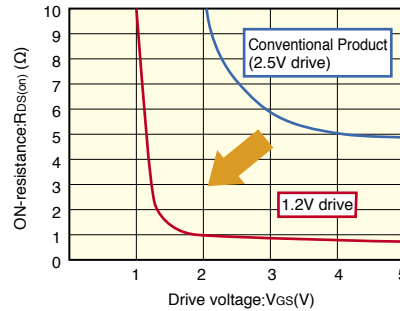
## Applications

General load switch drives, LED lamp drives, Muting circuits, DC/DC converters, Switch for charger control, and the like.

## Stable low voltage drive

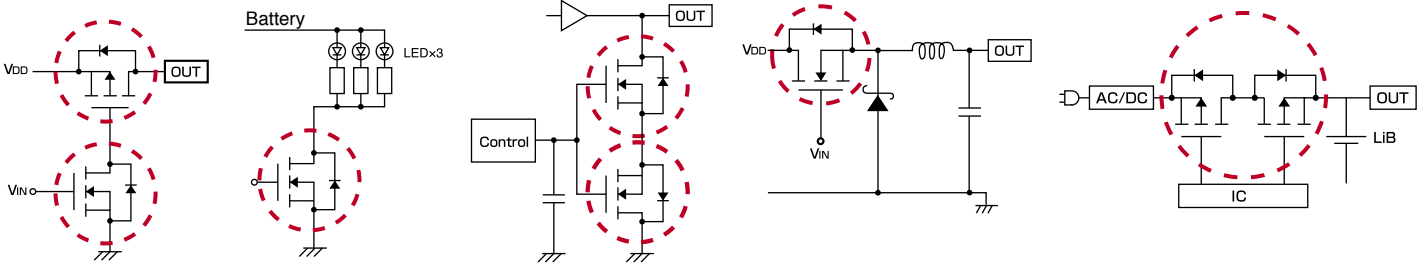
A new low-voltage drive process ensures stable operation at  $V_{GS} = 1.2V$ . ON-resistance is also significantly reduced compared to conventional 2.5V products, resulting in 20 to 85% less power consumption when ON.

### ON-resistance comparison



## Circuit example

- Load switch drive
- LED lamp driver
- Muting circuit
- DC/DC Converters
- Switch for charger control



## Lineup

Package	Pd(W)	Polarity	Part No.	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)	R <sub>DS(on)</sub> Typ.(m $\Omega$ )			Drive Voltage (V)	Internal Circuitry
						V <sub>GS</sub> =1.5V	V <sub>GS</sub> =2.5V	V <sub>GS</sub> =4.5V		
VMT3	0.15	Nch	New RUM002N02	20	0.2	1.6 $\Omega$ *1	0.8 $\Omega$	0.1 $\Omega$	1.2	-
			RUM003N02	20	0.3	1 $\Omega$ *2	0.8 $\Omega$	0.7 $\Omega$ *3	1.8	-
		Pch	New RZM002P02	-20	-0.2	2.4 $\Omega$ *1	1 $\Omega$	0.8 $\Omega$	1.2	-
EMT3	0.15	Nch	New RUE002N02	20	0.2	1.6 $\Omega$ *1	0.8 $\Omega$	0.1 $\Omega$	1.2	-
			RUE003N02	20	0.3	1 $\Omega$ *2	0.8 $\Omega$	0.7 $\Omega$	1.8	-
		Pch	New RZE002P02	-20	-0.2	2.4 $\Omega$ *1	1 $\Omega$	0.8 $\Omega$	1.2	-
EMT6	0.15	Nch+Nch	New EM6K7	20	0.2	1.6 $\Omega$ *1	0.8 $\Omega$	0.7 $\Omega$	1.2	⑨
			EM6K6	20	0.3	1 $\Omega$ *2	0.8 $\Omega$	0.7 $\Omega$	1.8	⑨
		Pch+Pch	New EM6J1	-20	-0.2	2.4 $\Omega$ *1	1 $\Omega$	0.8 $\Omega$	1.2	⑪
			New EM6M2	20	0.3	1.6 $\Omega$ *1	0.8 $\Omega$	0.7 $\Omega$	1.2	⑩
TUMT3	0.8	Nch	RUF015N02	20	1.5	220*2	170	130	1.8	-
			New RUF020N02	20	2	170	95	75	1.5	-
			RUF025N02	20	2.5	80	49	39	1.5	-
		Pch	New RZF013P01	-12	-1.3	530	280	190	1.5	-
			New RZF020P01	-12	-2	200	105	75	1.5	-
			RZF030P01	-12	-3	72	39	28	1.5	-

Package	Pd(W)	Part No.	Part No.	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)	R <sub>DS(on)</sub> Typ.(m $\Omega$ )			Drive Voltage (V)	Internal Circuitry
						V <sub>GS</sub> =1.5V	V <sub>GS</sub> =2.5V	V <sub>GS</sub> =4.5V		
TUMT6	1	Nch	RUL035N02	20	3.5	66	38	31	1.5	-
			Pch	New RZL025P01	-12	-2.5	110	60	44	1.5
		Nch+Nch	RZL035P01	-12	-3.5	66	36	26	1.5	-
			US6K4	20	1.5	300	170	130	1.8	⑨
		Nch+Pch	New US6J11	-12	-1.3	530	280	190	1.5	⑪
			New US6M11	20	1.5	300	170	130	1.8	⑩
TSMT3	1	Nch	New RUR020N02	20	2	170	95	75	1.5	-
			RUR040N02	20	4	55	33	25	1.5	-
		Pch	New RZR020P01	-12	-2	200	105	75	1.5	-
			New RZR025P01	-12	-2.5	110	60	44	1.5	-
			RZR040P01	-12	-4	55	30	22	1.5	-
			RZR050P01	-12	-5	44	26	19	1.5	-
TSMT5	1.25	Nch+SBD(0.5A)	QS5U34	20	1.5	220*2	170	130	1.8	②
		Nch+SBD(0.7A)	QS5U36	20	2.5	120	74	58	1.5	②
TSMT6	1.25	Nch	RUQ050N02	20	5	40	27	22	1.5	-
			Pch	New RZQ045P01	-12	-4.5	50	31	25	1.5
		Pch+Pch	RZQ050P01	-12	-5	44	26	19	1.5	-
			New QS6J11	-12	-2	200	105	75	1.5	⑪

Note) Please see p.16 for the internal circuitry

\*1  $V_{GS}=1.2V$  \*2  $V_{GS}=1.8V$  \*3  $V_{GS}=4V$

# ECOMOS™ Series ②

## WEMT6 / TSST8 / TSMT8 Package

### Features

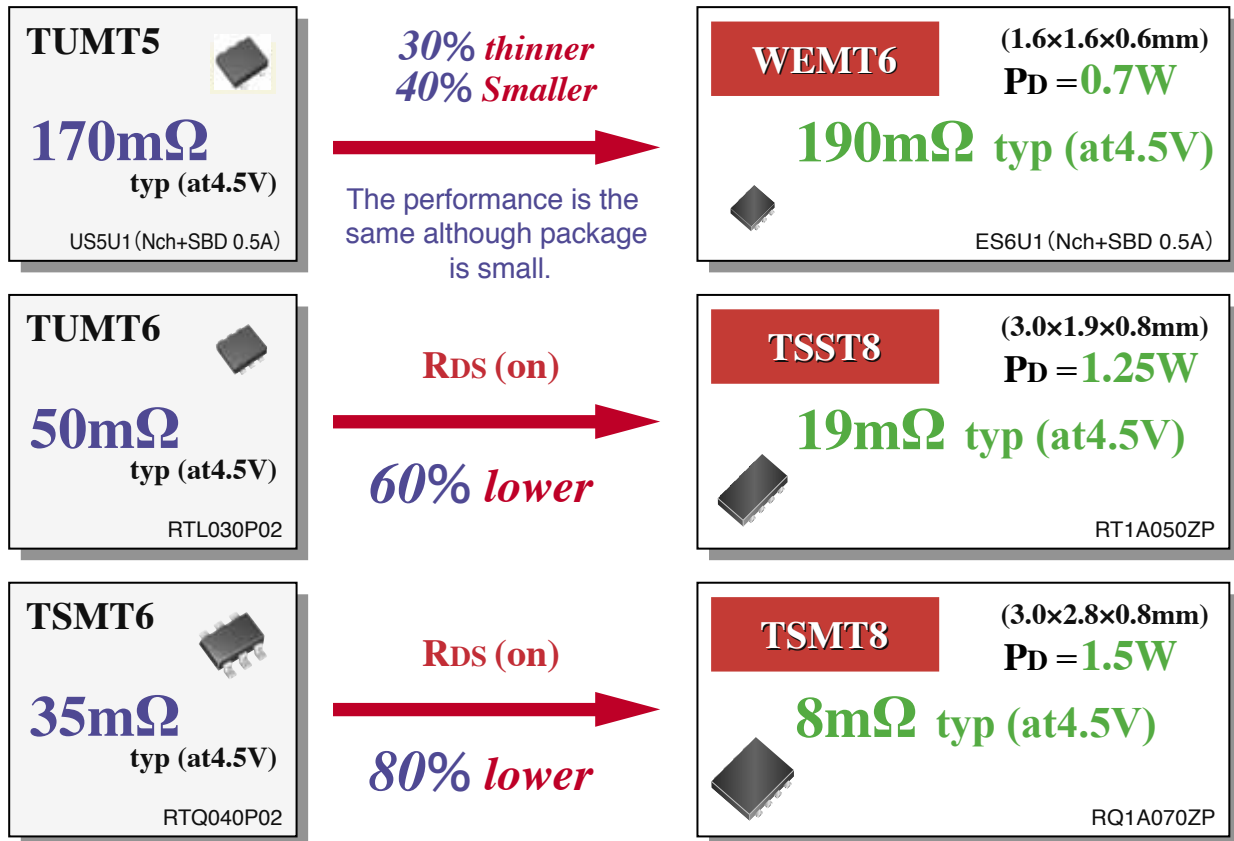
- Low ON-resistance more than conventional products
- **Thin and small packages**
- Matching to a highly effective, high density mounting.

### Advantage

- Small and high-power
- Low ON-resistance compared with conventional products

### Benefit

- **Energy saving**
- **Space saving**



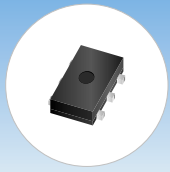
## Lineup

Package	Pd(W)	Polarity	Part No.	Vdss(V)	Id(A)	Rds(on) Typ.(mΩ)				Drive Voltage (V)	Internal Circuitry
						Vgs=1.5V	Vgs=1.8V	Vgs=2.5V	Vgs=4.5V		
WEMT6	0.7	Nch	<b>New</b> RW1C015UN	20	1.5	300	220	170	130	1.8	—
			<b>New</b> RW1C020UN	20	2	170	—	95	75	1.5	—
		Nch+SBD (0.5A)	<b>New</b> ES6U2	20	1.5	300	220	170	130	1.8	②
		Pch	<b>New</b> RW1A013ZP	-12	-1.3	530	—	280	190	1.5	—
			<b>New</b> RW1A020ZP	-12	-2	200	—	105	75	1.5	—
Pch+SBD (0.5A)	<b>New</b> ES6U1	-12	-1	530	—	280	190	1.5	②		
TSST8	1.25	Pch	<b>New</b> RT1A040ZP	-12	-4	55	—	30	22	1.5	—
			<b>New</b> RT1A050ZP	-12	-5	48	—	26	19	1.5	—
		Pch+Pch	TT8J1	-12	-2.5	110	—	60	44	1.5	⑫
			TT8J21	-20	-2.5	140	100	68	49	1.5	⑫
Pch+SBD (1A)	TT8U1	-20	-2.4	180	150	105	80	1.5	⑧		
TSMT8	1.5	Pch	<b>New</b> RQ1A060ZP	-12	-6	39	—	22	16	1.5	—
			<b>New</b> RQ1A070ZP	-12	-7	19	—	11	8	1.5	—
		Pch+Pch	<b>New</b> QS8J1	-12	-4.5	48	—	28	21	1.5	⑫

Note) Please see p.16 for the internal circuitry

# MPT6 Package Dual MOSFETs

## MP6K, MP6M Series



### Features

High power  
Space saving  
High performance

The frame pattern was optimized to create a compact package requiring 40% less mounting area while delivering the same package power as the conventional SOP8.

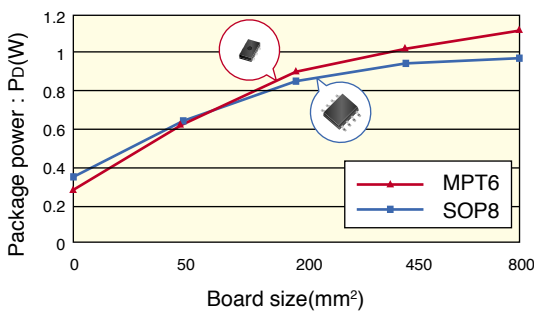
### Summary

### Applications

DC/DC Converters,  
Motor drive circuit,  
Amusement equipment

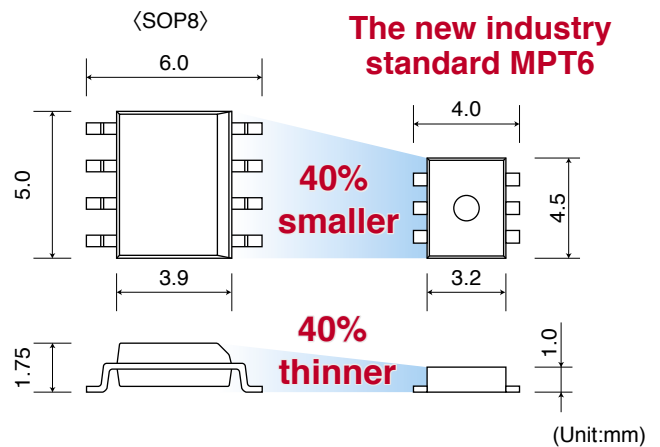
### Excellent package power

Provides the same package power as the SOP8 (5060 size) in the 4540 size.



### Space-saving, Thin, Low ON-resistance

Delivers the same low ON-resistance as the SOP8 (5060 size) in a package 40% smaller and 40% thinner.



### Outline



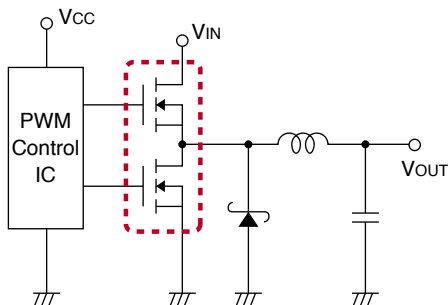
Front side



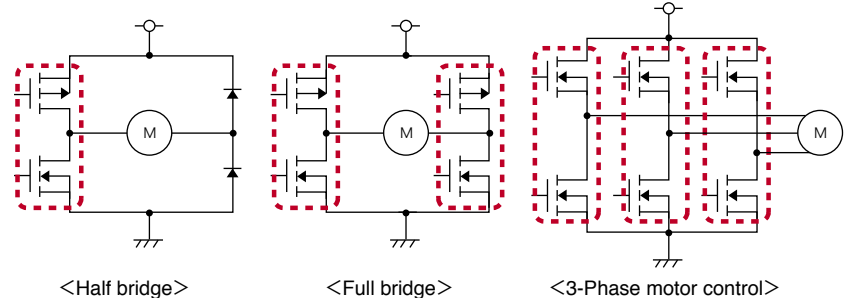
Back side

### Circuit example

#### DC/DC Converters



#### Motor drive circuit



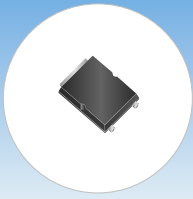
### Lineup

Package	Pd(W)	Polarity	品名	Vdss(V)	Ib(A)	Rbs(on) Typ.(mΩ)			Qg(nC) VGS=5V	Internal Circuitry
						VGS=4V	VGS=4.5V	VGS=10V		
MPT6	2.0	Nch+Nch	MP6K65	30	3.5	105	95	73	2	⑨
			MP6K61	30	5	55	50	36	4	
			MP6K62	30	6	33	30	24	7.6	
		Nch+Pch	MP6M63	30	5	55	50	36	4	⑩
				-30	-4.5	60	55	40	8.4	
			MP6M62	30	3.5	107	93	63	2	
			-30	-3.5	110	100	70	4.6		

Note) Please see p.16 for the internal circuitry



# TCPT3 Package MOSFETs



## Features

Thin  
High power

## Summary

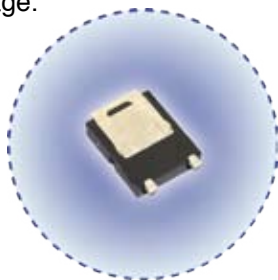
The same mounting space as the one for conventional CPT3 package : yet more current is applicable.

## Applications

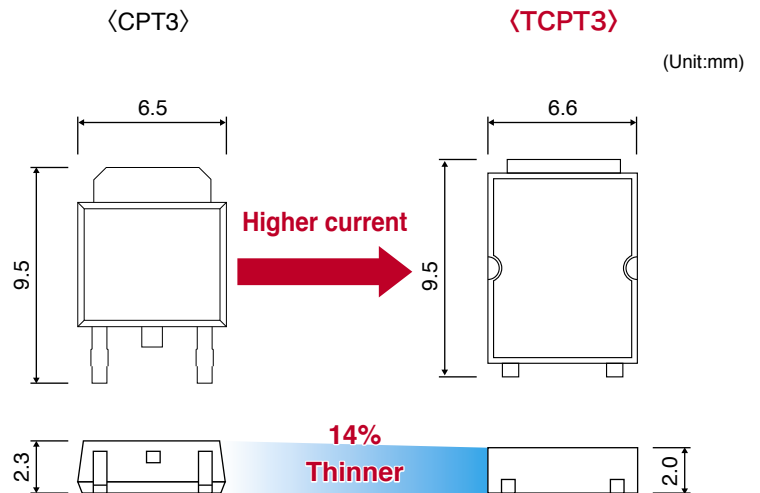
LCD backlight inverters  
Motor drive circuit

## High power, Thin

Improvement of heat-radiation efficiency has enabled higher current intake with the same mounting space as the one for conventional CPT3 package.



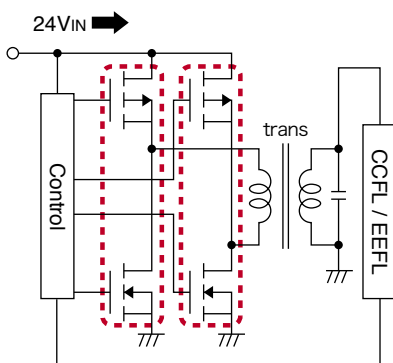
TCPT3 (Back side)



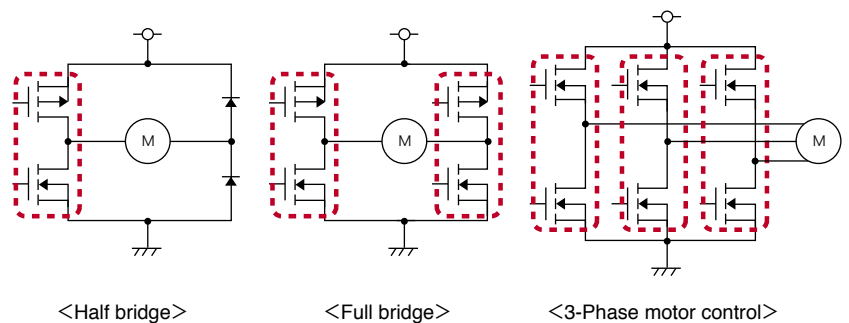
## Circuit example

Controlling heat emission is a major challenge with large LCDs. The high power TCPT3 package helps reduce heat dissipation in the backlight inverter circuit.

### LCD backlight inverter circuit



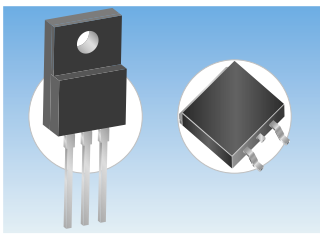
### Motor drive circuit



## Lineup

Package	Pd(W)	Polarity	Part No.	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)	R <sub>ds(on)</sub> Typ.(mΩ)			Q <sub>g</sub> (nC) V <sub>GS</sub> =5V
						V <sub>GS</sub> =4V	V <sub>GS</sub> =4.5V	V <sub>GS</sub> =10V	
TCPT3	20	Nch	RSY300N04	40	30	11	10	8	24
			RSY200N05	45	20	28	25	20	12
		Pch	RSY160P05	-45	-16	50	45	35	17

# High-speed Switching High Voltage Resistance MOSFETs



## Features

High power  
Energy saving  
High performance

## Summary

This high-performance series was developed using a new high voltage resistance process that enables fast switching and low ON-resistance.

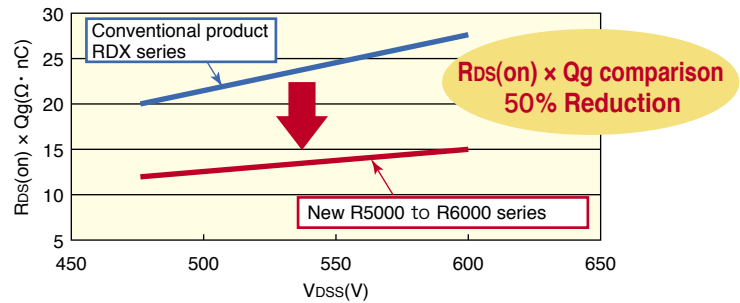
## Applications

Switching power supplies  
Lighting

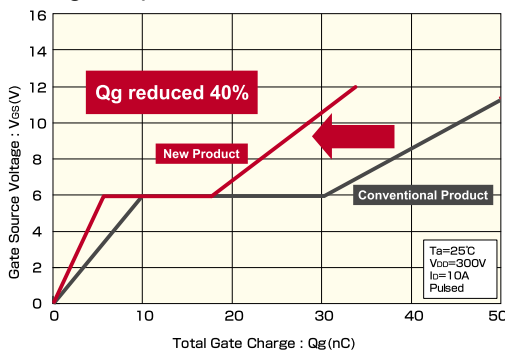
## High-speed switching (Low switching loss)

A new low ON-resistance process reduces ON-resistance by 50% over conventional units, significantly improving switching speed (by 30%) while reducing switching loss. The lineup is available in two different power packages, TO-220FM and LPT, featuring lower heat emission.

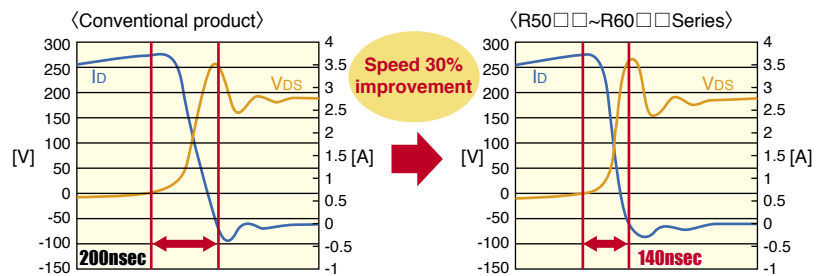
### ■ $R_{DS(on)} \times Q_g$ comparison



### ■ $Q_g$ comparison



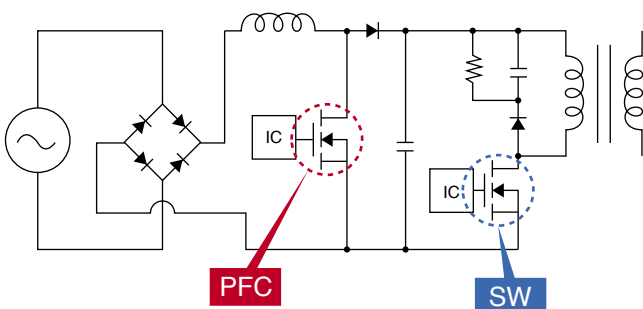
### ■ Switching speed comparison



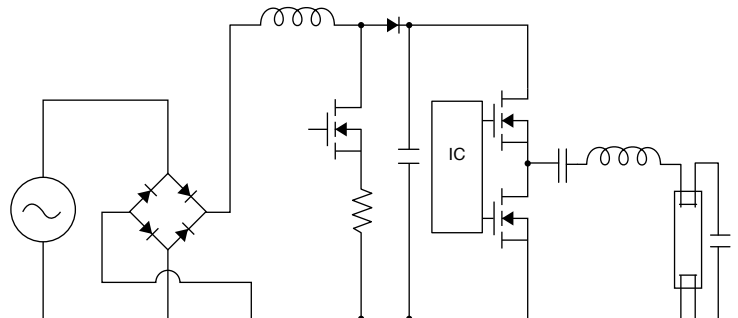
## Circuit example

Ideal for use in the PFC block, requiring low ON-resistance, and in switching (SW) circuits in the switching power supply, where switching speed is of critical importance. Also, it is suitable also for the ballast circuit of the lighting.

### ■ Switching power supply circuit (Primary)



### ■ Ballast circuit



## Lineup

Package	Pd(W)	Polarity	Part No.	V <sub>BS</sub> (V)	I <sub>D</sub> (A)	R <sub>BS(on)</sub> Typ.(Ω) V <sub>GS</sub> =10V	Q <sub>g</sub> (nC) V <sub>GS</sub> =10V	
CPT3	40	Nch	<b>New</b> R4008AND	400	8	0.73	15	
			<b>New</b> R5205CND	525	5	1.3	9.5	
			<b>New</b> R5207AND	525	7	0.78	13	
			<b>New</b> R6004AND	600	4	1.5	10	
			<b>New</b> R6006AND	600	6	0.9	15	
LPT	40	Nch	R5007ANJ	500	7	0.8	13	
	50	Nch	R5009ANJ	500	9	0.55	21	
	75	Nch	<b>New</b> R5011ANJ	500	11	0.38	30	
	100	Nch	<b>New</b> R5013ANJ	500	13	0.29	35	
			R5016ANJ	500	16	0.21	50	
			<b>New</b> R5019ANJ	500	19	0.18	52	
			<b>New</b> R5021ANJ	500	21	0.17	64	
			<b>New</b> R6012ANJ	600	12	0.32	35	
			<b>New</b> R6015ANJ	600	15	0.23	60	
			<b>New</b> R6018ANJ	600	18	0.21	53	
			<b>New</b> R6020ANJ	600	20	0.19	65	
	TO-220FM	40	Nch	R5007ANX	500	7	0.8	13
		50	Nch	<b>New</b> R5005CNX	500	5	1.3	9.5
R5009ANX				500	9	0.55	21	
<b>New</b> R5011ANX				500	11	0.38	30	
R5013ANX				500	13	0.29	35	
R5016ANX				500	16	0.21	50	
<b>New</b> R5019ANX				500	19	0.18	52	
<b>New</b> R5021ANX				500	21	0.16	64	
R6008ANX				600	8	0.6	21	
<b>New</b> R6010ANX				600	10	0.43	25	
<b>New</b> R6012ANX				600	12	0.32	35	
<b>New</b> R6015ANX				600	15	0.23	50	
<b>New</b> R6018ANX				600	18	0.21	53	
<b>New</b> R6020ANX				600	20	0.17	65	
TO-3PF	200	Nch	★ R6025ANZ	600	25	0.12	85	

★ : Under Development

## Small signal MOSFETs

Package	Pd(W)	Polarity	Part No.	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)	R <sub>ds(on)</sub> Typ.(Ω)			
						V <sub>GS</sub> =2.5V	V <sub>GS</sub> =4V	V <sub>GS</sub> =4.5V	V <sub>GS</sub> =10V
VMT3	0.15	Nch	<b>2SK3541</b>	30	0.1	7	5	–	–
		Pch	<b>RTM002P02</b>	–20	–0.2	2.0	1.1	1.0	–
			<b>RSM002P03</b>	–30	–0.2	–	1.6	1.4	0.9
EMT3	0.15	Nch	<b>2SK3019</b>	30	0.1	7	5	–	–
		Pch	<b>RTE002P02</b>	–20	–0.2	2.0	1.1	1.0	–
			<b>RSE002P03</b>	–30	–0.2	–	1.6	1.4	0.9
EMT5	0.15	Nch+Nch	<b>EM5K5</b>	30	0.3	0.8	0.7	0.6	–
EMT6	0.15	Nch+Nch	<b>EM6K1</b>	30	0.1	7	5	–	–
		Nch+Pch	<b>EM6M1</b>	30	0.1	7	5	–	–
				–20	–0.2	2	1.1	1	–
UMT3	0.2	Nch	<b>2SK3018</b>	30	0.1	7	5	–	–
			<b>RJU003N03</b>	30	0.3	1.4	0.9	0.8	–
			<b>RHU003N03</b>	30	0.3	–	1.4	1.2	0.8
			<b>RJU002N06</b>	60	0.2	2.2	1.7	1.6	–
			<b>RHU002N06</b>	60	0.2	–	2.8	–	1.7
		Pch	<b>RTU002P02</b>	–20	–0.25	2.0	1.1	1.0	–
			<b>RSU002P03</b>	–30	–0.25	–	1.6	1.4	0.9
UMT5	0.15	Nch+Nch	<b>UM5K1N</b>	30	0.1	7	5	–	–
UMT6	0.15	Nch+Nch	<b>UM6K1N</b>	30	0.1	7	5	–	–
		Pch+Pch	<b>New UM6J1N</b>	–30	–0.2	–	1.6	1.4	0.9
SST3	0.2	Nch	<b>RK7002</b>	60	0.115	–	–	7.5 max.*	7.5 max.
			<b>RK7002A</b>	60	0.3	–	1.1	–	0.7
SMT3	0.2	Nch	<b>2SK2731</b>	30	0.2	–	2.8	–	1.5
			<b>RJK005N03</b>	30	0.5	0.65	0.42	0.40	–
			<b>RHK005N03</b>	30	0.5	–	0.6	0.51	0.35
			<b>RHK003N06</b>	60	0.3	–	1.1	–	0.7
SMT6	0.2	Nch+Nch	<b>SM6K2</b>	60	0.2	–	2.8	–	1.7

\* V<sub>GS</sub>=5V

Middle Power MOSFETs

Package	Pd(W)	Polarity	Part No.	Vdss(V)	Id(A)	Rds(on) Typ.(mΩ)				Qg(nC) Vgs=4.5V
						Vgs=2.5V	Vgs=4V	Vgs=4.5V	Vgs=10V	
WEMT6	0.7	Nch	<b>New</b> RW1E014SN	30	1.4	–	270	250	170	1.4 *
		Nch+SBD(0.5A)	<b>New</b> ES6U3	30	1.4	–	270	250	170	1.4 *
TUMT3	0.8	Nch	RTF015N03	30	1.5	240	180	170	–	1.6
			RTF025N03	30	2.5	70	50	48	–	3.7
			RSF014N03	30	1.4	–	270	250	170	1.4 *
		Pch	RTF010P02	–20	–1	570	310	280	–	2.1
			RTF015P02	–20	–1.5	180	110	100	–	5.2
			RTF020P02	–20	–2	120	65	60	–	7
TUMT5	1	Nch+SBD(0.7A)	US5U3	30	1.5	240	180	170	–	1.6
		Nch+SBD(0.5A)	US5U1	30	1.5	240	180	170	–	1.6
			US5U2	30	1.4	–	270	250	170	1.4 *
		Pch+SBD(0.5A)	US5U30	–20	–1	570	310	280	–	2.1
		Pch+SBD(0.1A)	US5U35	–45	–0.7	–	1000	900	600	1.7 *
TUMT6	1	Nch	RTL035N03	30	3.5	56	42	40	–	4.6
			US6K1	30	1.5	240	180	170	–	1.6
		Nch+Nch	US6K2	30	1.4	–	270	250	170	1.4 *
			US6U37	30	1.5	240	180	170	–	1.6
		Pch	RTL020P02	–20	–2	180	110	100	–	4.9
			RTL030P02	–20	–3	90	55	50	–	8
			RSL020P03	–30	–2	–	140	125	80	3.9 *
		Pch+Pch	US6J2	–20	–1	570	310	280	–	2.1
		Nch+Pch	US6M2	30	1.5	240	180	170	–	1.6
			US6M1	30	1.4	–	270	250	170	1.4 *
TSMT3	1	Nch	RTR025N03	30	2.5	95	70	66	–	3.3
			RTR040N03	30	4	47	36	34	–	5.9
			<b>New</b> RRR035N03	30	3.5	–	65	60	45	4.5 *
			RSR025N03	30	2.5	–	83	74	50	2.9 *
			<b>New</b> RTR030N05	45	3	68	53	48	–	6.2
			<b>New</b> RTR025N05	45	2.5	125	100	95	–	3.2
			RTR020N05	45	2	180	135	130	–	2.9
			<b>New</b> RSR030N06	60	3	–	75	70	60	5 *
		<b>New</b> RSR020N06	60	2	–	150	140	120	2.7 *	
		Pch	RTR011P02	–20	–1.1	570	310	280	–	2
			RTR020P02	–20	–2	180	110	100	–	4.9
			RTR025P02	–20	–2.5	115	75	70	–	7
			RTR030P02	–20	–3	90	60	55	–	9.3
			<b>New</b> RRR030P03	–30	–3	–	95	85	55	5.2 *
RSR025P03	–30		–2.5	–	115	100	70	5.4 *		
RSR020P03	–30	–2	–	150	135	85	4.3 *			
RSR015P03	–30	–1.5	–	320	270	170	2.6 *			
TSST8	1.25	Pch+Pch	<b>New</b> TT8J2	–30	–2.5	–	115	95	60	4.8 *
		Nch+Nch	<b>New</b> TT8K2	30	2.5	95	70	65	–	3.2
		Pch+Nch	<b>New</b> TT8M2	30	2.5	95	70	65	–	3.2
			–20	–2.5	68	–	49	–	12	
TSMT5	1.25	Nch+Nch	QS5K2	30	2	110	76	71	–	2.8
			QS5U12 *3	30	2	110	76	71	–	2.8
		Nch+SBD(1A)	QS5U17 *3	30	2	110	76	71	–	2.8
			QS5U13 *4	30	2	110	76	71	–	2.8
		Nch+SBD(0.5A)	QS5U16 *4	30	2	110	76	71	–	2.8
			QS5U28	–20	–2	175	97	90	–	4.8
		Pch+SBD(1A)	QS5U21 *5	–20	–1.5	260	180	160	–	4.2
			QS5U27 *5	–20	–1.5	260	180	160	–	4.2
			QS5U33	–30	–2	–	160	145	95	3.4 *
		Pch+SBD(0.5A)	QS5U23 *6	–20	–1.5	260	180	160	–	4.2
QS5U26 *6	–20		–1.5	260	180	160	–	4.2		

\*3,4,5,6: Please note that, although the internal circuit configuration may differ between part numbers, the electrical specifications remain the same.

\*Vgs=5V

Middle Power MOSFETs

Package	Pd(W)	Polarity	Part No.	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)	R <sub>DS(on)</sub> Typ.(mΩ)				Q <sub>g</sub> (nC)
						V <sub>GS</sub> =2.5V	V <sub>GS</sub> =4V	V <sub>GS</sub> =4.5V	V <sub>GS</sub> =10V	V <sub>GS</sub> =4.5V
TSM <sub>T</sub> 6	1.25	Nch	RTQ020N03	30	2	138	94	89	–	2.4
			RTQ035N03	30	3.5	55	40	38	–	4.6
			RTQ045N03	30	4.5	42	32	30	–	7.6
			RSQ045N03	30	4.5	–	40	36	27	6.8 *
			<b>New</b> RRQ035N03	30	3.5	–	65	60	45	4.5 *
			RSQ035N03	30	3.5	–	67	60	44	5.3 *
			RSQ020N03	30	2	–	168	148	96	2.2 *
			<b>New</b> RTQ020N05	45	2	200	150	140	–	2.3
			RVQ040N05	45	4	–	53	47	38	6.3
		<b>New</b> RSQ015N06	60	1.5	–	255	240	210	2 *	
		Nch+Nch	QS6K1	30	1	260	180	170	–	1.7
		Pch	RTQ025P02	–20	–2.5	140	80	72	–	6.4
			RTQ030P02	–20	–3	110	65	60	–	9
			RTQ035P02	–20	–3.5	80	55	50	–	10.5
			RTQ040P02	–20	–4	60	40	35	–	12.2
			RSQ025P03	–30	–2.5	–	145	120	80	4.4 *
			<b>New</b> RRQ030P03	–30	–3	–	95	85	55	5.2 *
			RSQ030P03	–30	–3	–	100	90	60	6 *
		Pch+Pch	RSQ035P03	–30	–3.5	–	70	65	45	9.2 *
			QS6J1	–20	–1.5	310	170	155	–	3
		Nch+Pch	QS6J3	–20	–1.5	310	170	155	–	3
			QS6M3	30	1.5	260	180	170	–	1.6
		–20		–1.5	310	170	155	–	3	
		Pch+SBD(0.5A)	QS6M4	30	1.5	260	180	170	–	1.6
–20	–1.5			310	170	155	–	3		
QS6U22	–20		–1.5	310	170	155	–	3		
QS6U24	–30		–1	–	600	500	300	1.7 *		
MPT3	*1 2.0	Nch	RHP030N03	30	3	–	160	–	90	–
			RJP020N06	60	2	210	170	165	–	–
			RHP020N06	60	2	–	240	200	150	–

\*1: When mounted on a ceramic board (40×40×0.7mm).

\*V<sub>GS</sub>=5V

Middle Power MOSFETs (SOP8)

Package	Pd(W)	Polarity	Part No.	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)	R <sub>DS(on)</sub> Typ.(mΩ)			Q <sub>g</sub> (nC)	
						V <sub>GS</sub> =4V	V <sub>GS</sub> =4.5V	V <sub>GS</sub> =10V	V <sub>GS</sub> =5V	
SOP8	2.0	Nch	RRS070N03	30	7	28	26	20	7.7	
			RRS090N03	30	9	18	17	14	12	
			RRS100N03	30	10	15	14	11	16	
			RRS110N03	30	11	11.5	11	9	22	
			RRS125N03	30	12.5	9.8	9.2	7.5	27	
			RRS130N03	30	13	9	8.5	7	30	
			RRS150N03	30	15	7	6.5	5.5	38	
			RRS180N03	30	18	4.8	4.5	3.8	63	
			RSS070N05	45	7	25	23	18	12	
			RSS080N05	45	8	20	18	15	13	
			RSS085N05	45	8.5	18	16	13	15.3	
			RSS095N05	45	9.5	15	14	11	18.9	
			RSS065N06	60	6.5	31	28	24	11	
			Nch+Nch	SP8K5	30	3.5	107	93	59	2.5
				SP8K1	30	5	58	52	36	3.9
				<b>New</b> SP8K62	30	6	33	30	24	7.6
		SP8K63		30	7	27	25	20	8.5	
		SP8K64		30	9	18	17	14	15	
		SP8K67		30	11	13.4	12.8	11	27	
		SP8K22		45	4.5	46	41	33	6.8	
		SP8K23		45	5	36	33	26	8.6	
		SP8K24		45	6	26	24	18	15.4	
		SP8K31		60	3.5	105	100	85	3.7	
		SP8K32		60	4.5	55	52	46	7	
		SP8K33		60	5	40	38	34	8	
		Nch+Nch+SBD	SP8K10S	30	7	25	23	17	8.4	
				30	8.5	19	17.8	14	8.9	

## Middle Power MOSFETs (SOP8)

Package	Pd(W)	polarity	Part No.	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)	R <sub>bs(on)</sub> Typ.(mΩ)			Q <sub>g</sub> (nC) V <sub>GS</sub> =5V
						V <sub>GS</sub> =4V	V <sub>GS</sub> =4.5V	V <sub>GS</sub> =10V	
SOP8	2.0	Pch	RRS040P03	-30	-4	95	85	55	5.2
			RRS050P03	-30	-5	58	52	36	9.2
			RRS075P03	-30	-7.5	25	22	15	21
			RRS090P03	-30	-9	17	15	11	30
			RRS100P03	-30	-10	14	12.5	9	39
			RRS140P03	-30	-14	7.3	6.7	5	80
			RSS060P05	-45	-6	38	35	26	23
			RSS070P05	-45	-7	28	25	19	34
		Pch+Pch	SP8J4	-30	-2	320	270	170	2.4
			SP8J3	-30	-3.5	120	100	65	5.5
			SP8J1	-30	-5	45	40	30	16
			SP8J62	-30	-4.5	60	55	40	8
			SP8J65	-30	-7	31	29	21.5	18
			SP8J66	-30	-9	19	17.5	13.5	35
		Nch+Pch	SP8M2	30	3.5	107	93	59	2.5
				-30	-3.5	120	100	65	5.5
			SP8M6	30	5	58	52	36	3.9
				-30	-3.5	120	100	65	5.5
			SP8M8	30	6	33	30	21	7.2
				-30	-4.5	65	57	40	8.5
			SP8M10	30	7	25	23	17	8.4
				-30	-4.5	65	57	40	8.5
			SP8M63	30	5	55	50	36	4
				-30	-4.5	60	55	40	8
			SP8M64	30	9	18	17	14	15
				-30	-7	31	29	21.5	18
			SP8M65	30	6	33	30	24	7.6
				-30	-7	31	29	21.5	18
			SP8M21	45	6	26	24	18	15.4
				-45	-4	47	43	33	20
			SP8M24	45	4.5	46	41	33	6.8
				-45	-3.5	66	60	45	13
		SP8M41	80	3.4	120	110	90	6.6	
-80	-2.6		230	220	165	8.2			
SP8M70	250	3	-	-	1.25Ω	5.2*			
	-250	-2.5	-	-	2.2Ω	8*			

\* V<sub>GS</sub>=10V

## Power MOSFETs (CPT3, TO-220FN, TO-220FM)

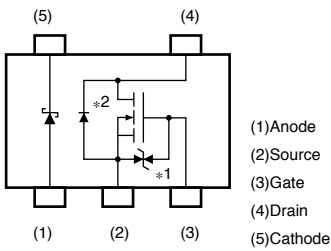
Package	Pd(W)	Polarity	Part No.	V <sub>DSS</sub> (V)	I <sub>D</sub> (A)	R <sub>DS(on)</sub> Typ.(Ω)	
						V <sub>GS</sub> =4V	V <sub>GS</sub> =10V
CPT3	10	Nch	<b>2SK2094</b>	60	2	0.4	0.3
	20	Nch	<b>New RSD220N06</b>	60	22	0.03	0.022
		Nch	<b>RSD200N10</b>	100	20	0.045	0.041
		Nch	<b>RDD050N20</b>	200	5	–	0.55
TO-220FN	30	Nch	<b>RDN050N20</b>	200	5	–	0.55
	35	Nch	<b>RDN100N20</b>	200	10	–	0.27
	40	Nch	<b>RDN150N20</b>	200	15	–	0.12
	35	Nch	<b>RDN080N25</b>	250	8	–	0.38
	40	Nch	<b>RDN120N25</b>	250	12	–	0.16
TO-220FM	35	Nch	<b>RDX050N50</b>	500	5	–	1.1
	40	Nch	<b>RDX080N50</b>	500	8	–	0.65
	45	Nch	<b>RDX120N50</b>	500	12	–	0.38
	30	Nch	<b>RDX030N60</b>	600	3	–	2.7
	35	Nch	<b>RDX045N60</b>	600	4.5	–	1.6
	40	Nch	<b>RDX060N60</b>	600	6	–	0.9
	45	Nch	<b>RDX100N60</b>	600	10	–	0.48



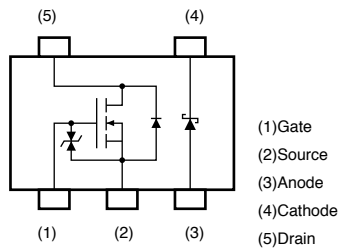
# Internal Circuitry

## ■ MOSFET + SBD

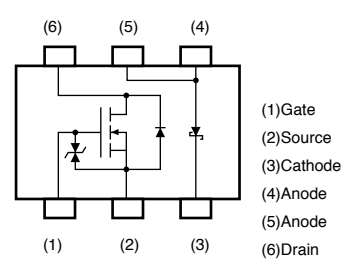
① Nch+SBD (A)



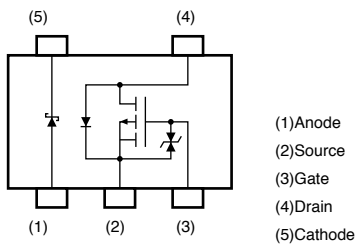
② Nch+SBD (B)



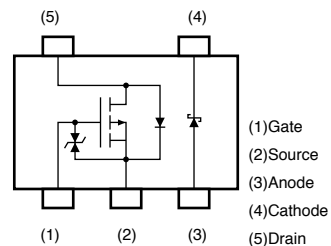
③ Nch+SBD (C)



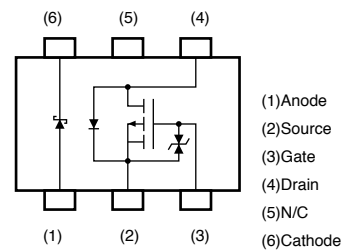
④ Pch+SBD (A)



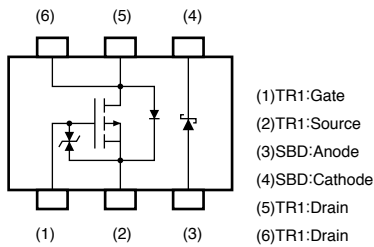
⑤ Pch+SBD (B)



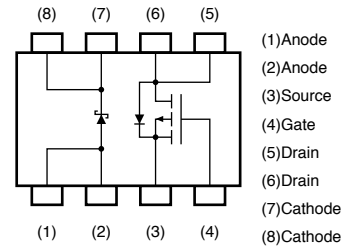
⑥ Pch+SBD (C)



⑦ Pch+SBD

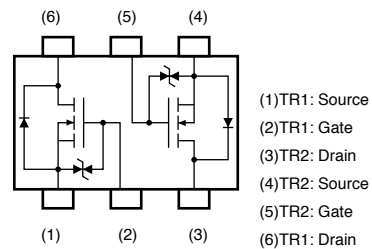


⑧ Pch+SBD (D)

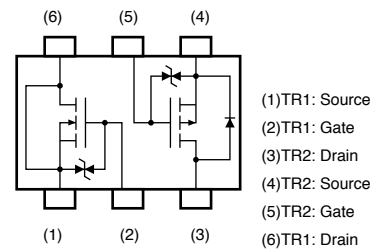


## ■ MOSFET Dual

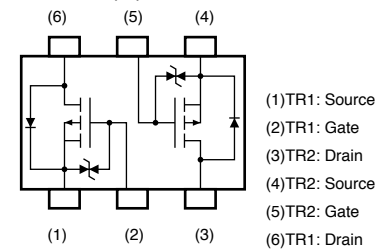
⑨ Nch+Nch



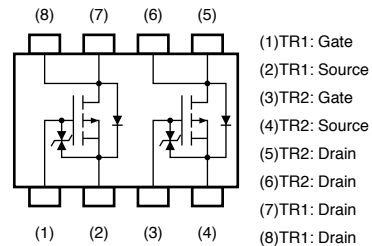
⑩ Nch+Pch



⑪ Pch+Pch (A)



⑫ Pch+Pch (B)



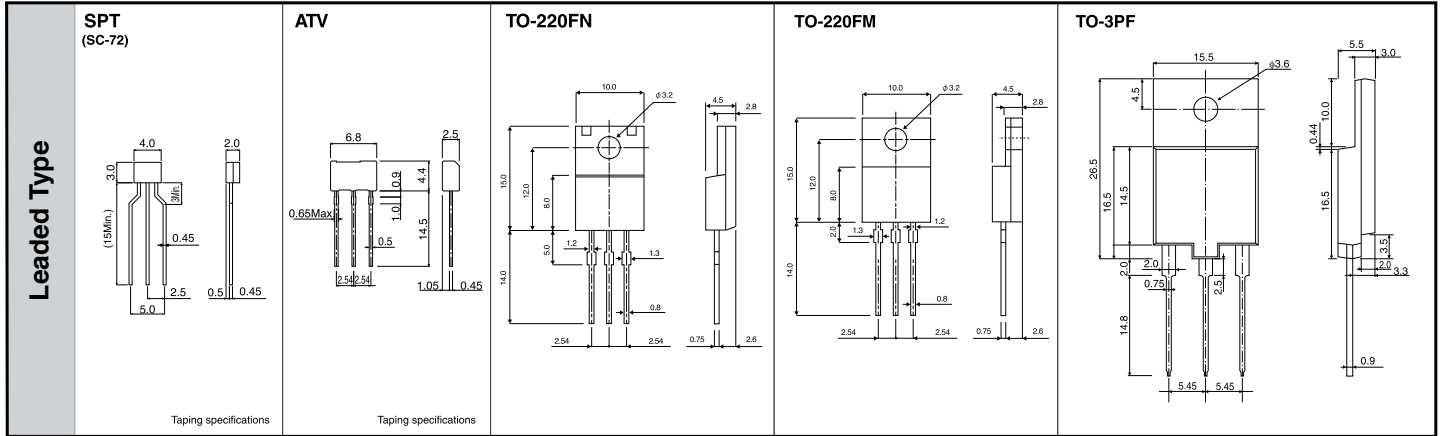
# Dimensions

(Unit : mm)

Surface Mount Type	<b>VMN3</b> 	<b>VMT3</b> 	<b>EMT3F</b> 	<b>EMT3 (SC-75A) &lt;SOT-416&gt;</b> 	<b>EMT5</b> 	<b>EMT6</b> 
	<b>UMT3F</b> 	<b>UMT3 (SC-70) &lt;SOT-323&gt;</b> 	<b>UMT5 (SC-88A) &lt;SOT-353&gt;</b> 	<b>UMT6 (SC-88) &lt;SOT-363&gt;</b> 	<b>SST3 &lt;SOT-23&gt;</b> 	
	<b>SMT3 (SC-59) &lt;SOT-346&gt;</b> 	<b>SMT5 (SC-74A)</b> 	<b>SMT6 (SC-74) &lt;SOT-457&gt;</b> 	<b>TSST8</b> 		
	<b>TUMT3</b> 	<b>TUMT5</b> 	<b>TUMT6</b> 	<b>WEMT6</b> 		
	<b>TSMT3</b> 	<b>TSMT5</b> 	<b>TSMT6</b> 	<b>TSMT8</b> 		
	<b>MPT3 (SC-62) &lt;SOT-89&gt;</b> 	<b>MPT6</b> 	<b>SOP8</b> 	<b>PSOP8S</b> 	<b>PSOP8</b> 	
	<b>CPT3 (SC-63) &lt;SOT-428&gt;</b> 	<b>TCPT</b> 	<b>LPTS</b> 	<b>LPTL</b> 		

Notes: 1) Characters in ( ) under package designation denotes JEITA No. Characters in <> under package designation denotes JEDEC No. 2) For details of dimensions, please refer to the technical specifications.

(Unit : mm)



Notes: 1) Characters in ( ) under package designation denotes JEITA No. Characters in <> under package designation denotes JEDEC No. 2) For details of dimensions, please refer to the technical specifications.



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